



FSS218 — N-Channel Silicon MOSFET

General-Purpose Switching Device

Applications

Features

- Motor drive applications.
- Inverter drive applications.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		35	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		8	A
Drain Current (PW≤10s)	I _D	Duty cycle≤1%	8.5	A
Drain Current (PW≤10μs)	I _{DP}	Duty cycle≤1%	32	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (2000mm ² ×0.8mm), PW≤10s	1.8	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0V	35			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =35V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.5		2.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =8A	5.4	9		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =8A, V _{GS} =10V		20	26	mΩ
	R _{DS(on)2}	I _D =4A, V _{GS} =4V		38	54	mΩ
Input Capacitance	C _{iss}	V _{DS} =10V, f=1MHz		1050		pF
Output Capacitance	C _{oss}	V _{DS} =10V, f=1MHz		200		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =10V, f=1MHz		140		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		17		ns
Rise Time	t _r	See specified Test Circuit.		65		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		75		ns
Fall Time	t _f	See specified Test Circuit.		45		ns

Marking : S218

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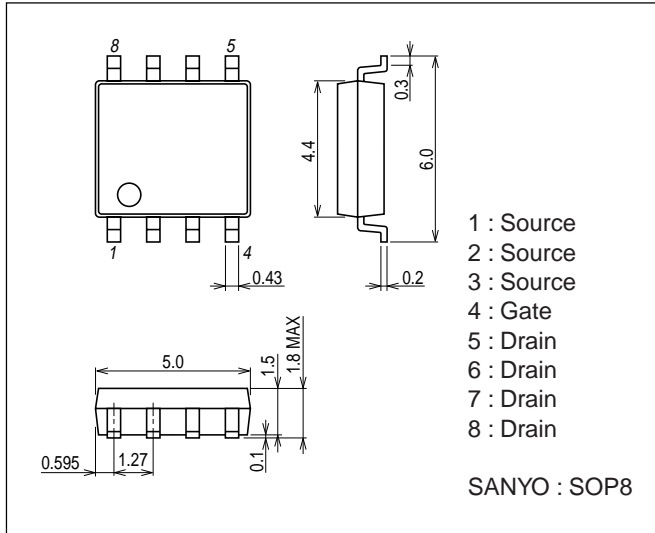
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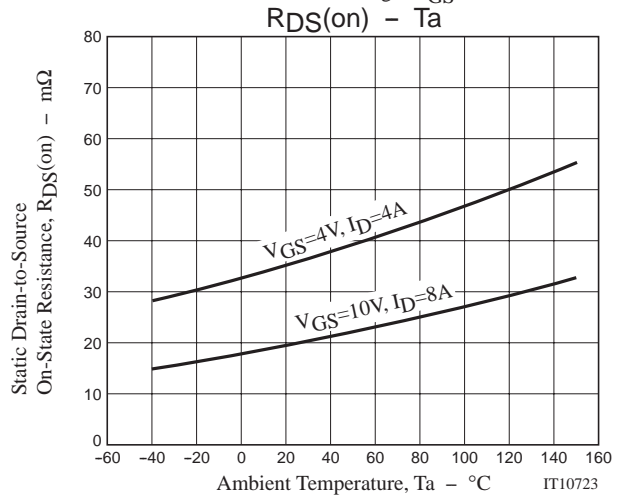
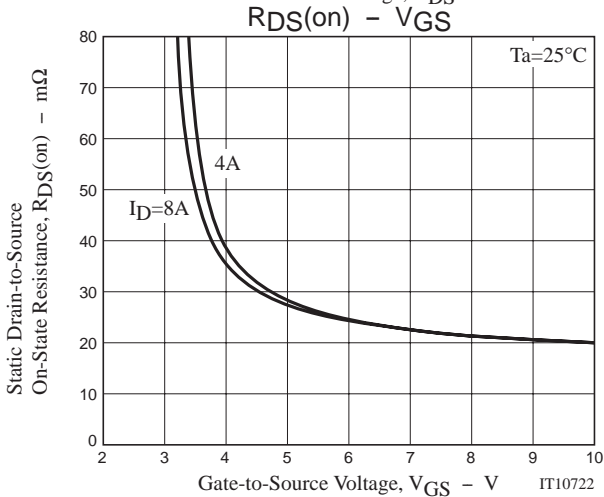
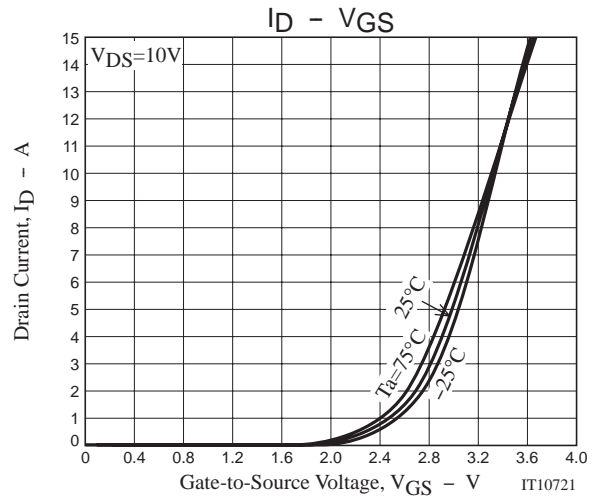
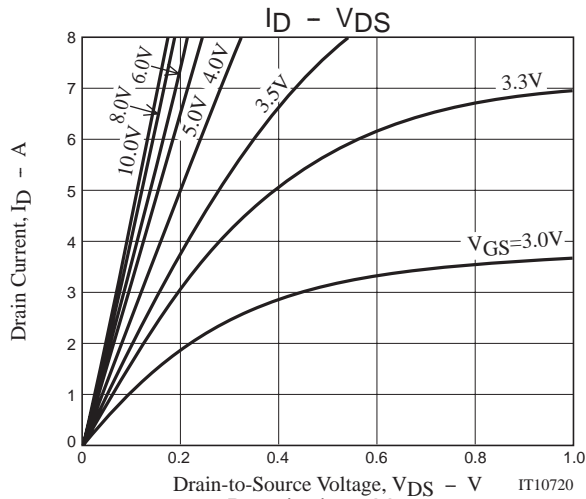
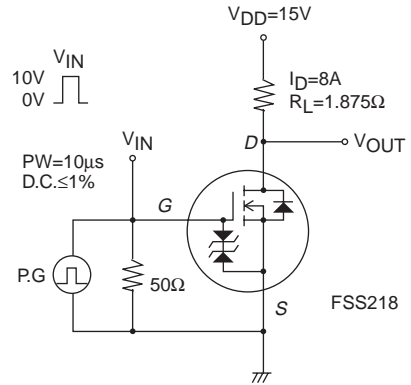
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =8A		19		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =8A		3.3		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =8A		3.5		nC
Diode Forward Voltage	V _{SD}	I _S =8A, V _{GS} =0V		0.85	1.2	V

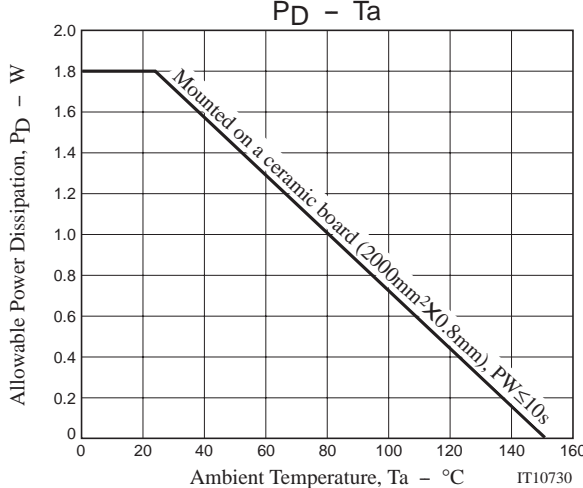
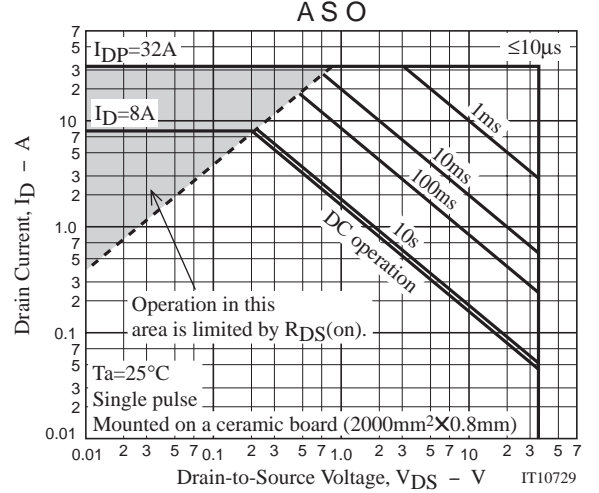
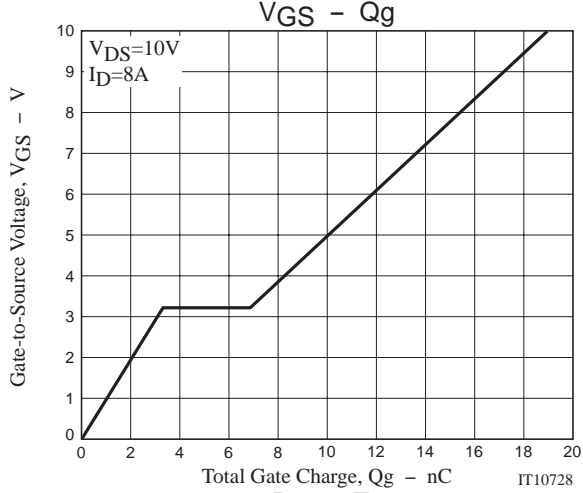
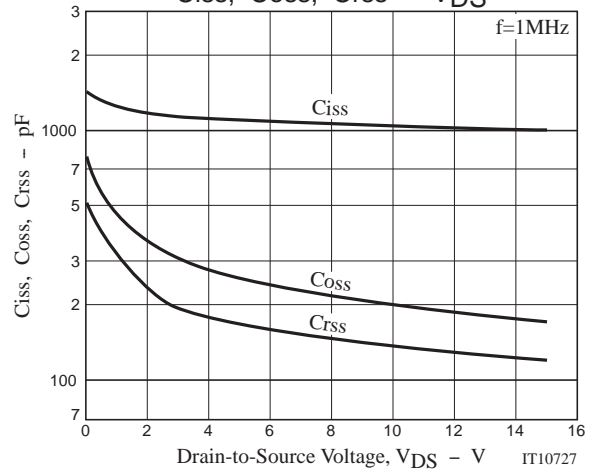
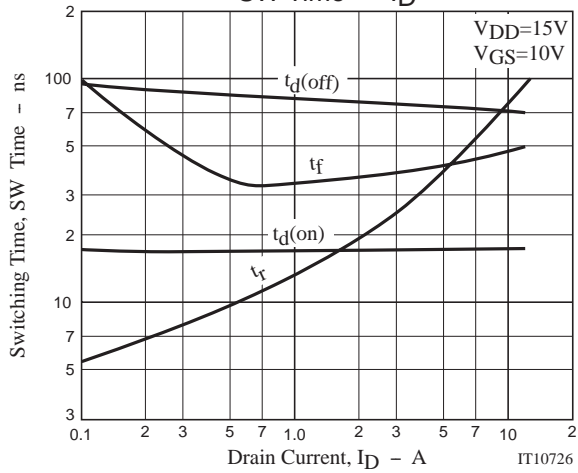
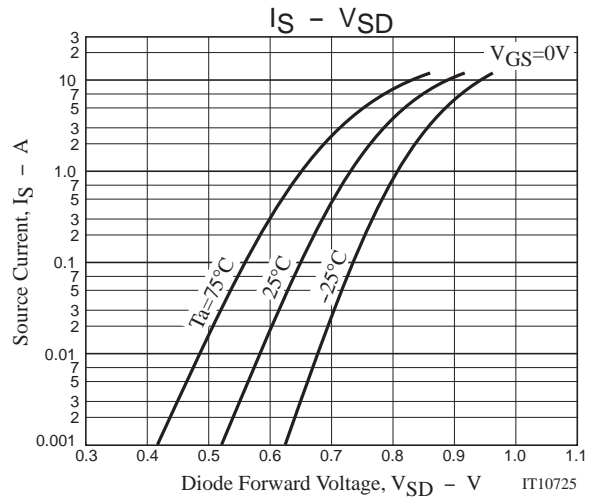
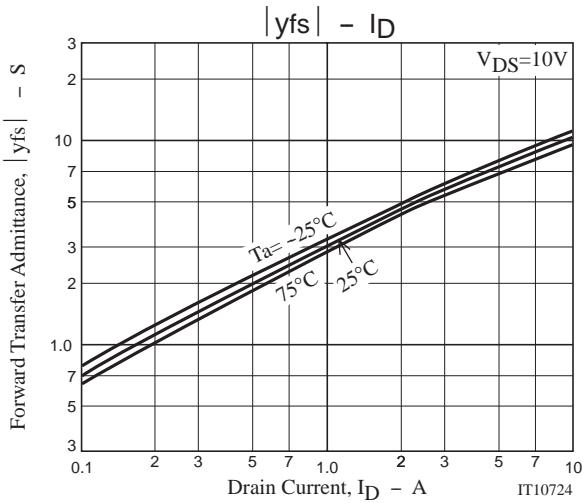
Package Dimensions

unit : mm
7005-002



Switching Time Test Circuit





Note on usage : Since the FSS218 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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